

DUAL PRECISION MICROPOWER CMOS VOLTAGE COMPARATOR WITH DRIVER

GENERAL DESCRIPTION

The ALD2303A/ALD2303 is a precision monolithic high performance dual voltage comparator built with advanced silicon gate CMOS technology. It features very high typical input impedance of $10^{12}\Omega$; low input bias current of 10pA; very low power dissipation of 7.5µA per comparator; and single (+5V) or dual (±5V) power supply operation.

The input voltage range includes ground, making this comparator ideal for single supply low level signal detection with high source impedance. The ALD2303A/ALD2303 can be used in connection with other voltage comparator circuits such as the ALD2301/ALD2302/ALD4302 voltage comparators. The output can be connected to a higher external voltage than V+.

The ALD2303A/ALD2303 is ideal for high precision micropower voltage comparator applications, especially low level signal detection circuits requiring low standby power, yet retaining high output current capability.

APPLICATIONS

- · Sensor detection circuits
- PCMCIA instruments
- MOSFET driver
- High source impedance voltage comparison circuits
- Multiple limit window comparator
- Power supply voltage monitor
- Photodetector sensor circuit
- High speed LED driver
- Oscillators
- Battery operated instruments
- Remote signal detection
- Multiple relay drivers

BENEFITS

- Extremely low power and high precision combination
- Built-in high input impedance buffer
- Built-in output driver with up to 60mA sink current

ORDERING INFORMATION ("L" suffix for lead free version)

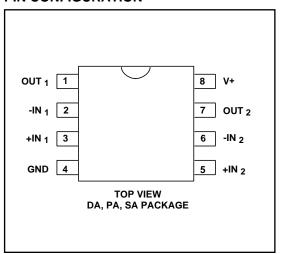
Operating Temperature Range *									
-55°C to +125°C	0°C to +70°C	0°C to +70°C							
8-Pin CERDIP Package	8-Pin Small Outline Package (SOIC)	8-Pin Plastic Dip Package							
ALD2303ADA ALD2303DA	ALD2303ASA ALD2303ASAL ALD2303SA ALD2303SAL	ALD23023PA ALD2303APAL ALD2303PA ALD2303PAL							

^{*} Contact factory for industrial temperature range

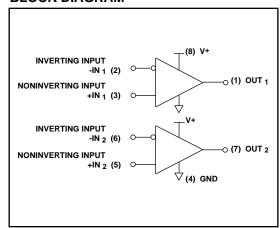
FEATURES

- 3V, 5V and 12V supply
- Guaranteed to drive 200Ω loads
- Fanout of 30LS TTL loads
- Guaranteed maximum supply current of 20µA for each comparator
- Pinout of LM193 type industry standard comparators
- Extremely low input bias currents -- 10pA
- Virtually eliminates source impedance effects
- Single (+5V) and dual supply (±5V) operation
- CMOS, NMOS and TTL compatible
- · Open drain wired-OR outputs
- · High output sinking current -- 60mA
- Low supply current spikes
- High gain -- 100V/mV

PIN CONFIGURATION



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Supply voltage, V ⁺		13.2V
Differential input voltage range		-0.3V to V ⁺ +0.3V
Power dissipation		600 mW
Operating temperature range	PA, SA package	0°C to +70°C
	DA package	55°C to +125°C
Storage temperature range		65°C to +150°C
Lead temperature, 10 seconds		+260°C

OPERATING ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}C$ V+= +5V unless otherwise specified

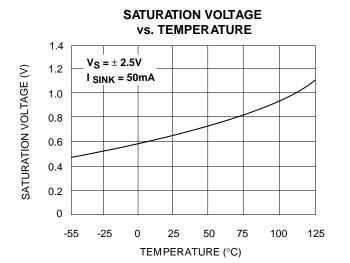
		2303A				2303			Test
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
Voltage Supply	V _S V+	±1.5 3		±6 12	±1.5 3		±6 12	V	Dual Supply Single Supply
Supply Current	Is		15	40		15	40	μА	RLOAD = ∞
Voltage Gain	A _{VD}	10	100		10	100		V/mV	RLOAD ≥15KΩ
Input Offset Voltage	Vos		1.0	2.0		3.0	5.0	mV	RLOAD =1.5KΩ
Input Offset Current ¹	los		10	200 800		10	200 800	рА	
Input Bias Current ¹	IB		10	200 1000		10	200 1000	рА	$0^{\circ}C \le T_A \le 70^{\circ}C$
Common Mode Input Voltage Range ²	VICR	-0.3		V+-1.5	-0.3		V+ -1.5	V	0°C ≤ T _A ≤ 70°C
Low Level Output Voltage	VoL		0.18	0.4		0.18	0.4	V	I _{SINK} =12mA V _{INPUT} =1V Differential
Low Level Output Current	l _{OL}	24	60		24	60		mA	V _{OL} =1.0V
High Level Leakage Current	I _{LH}		0.01	20		0.01	20	nA	V _{OH} = 5.0V
Response Time ²	tRP		6.5			6.5		μs	$R_L = 50 K\Omega$ $C_L = 15 pF$ 10 mV Input Step/10 mV Overdrive
			5			5		μs	RL = $50K\Omega$ C _L = $15pF$ TTL- Level Input Step

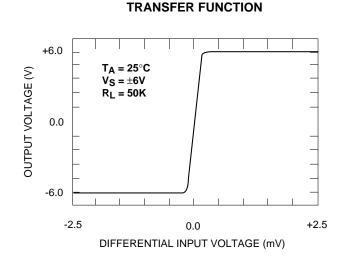
Notes:

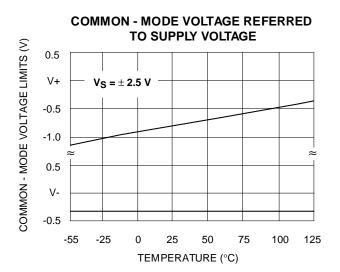
¹ Consists of junction leakage currents

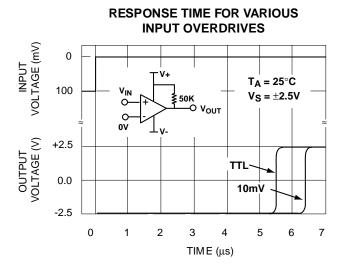
² Sample tested parameters

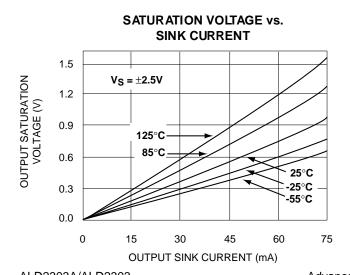
TYPICAL PERFORMANCE CHARACTERISTICS

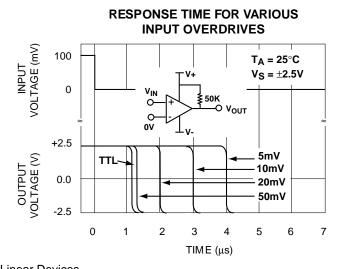






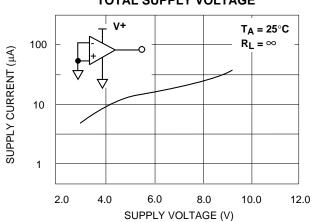




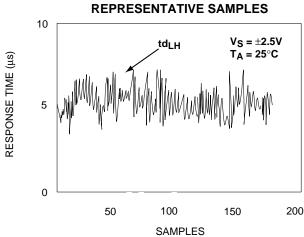


TYPICAL PERFORMANCE CHARACTERISTICS

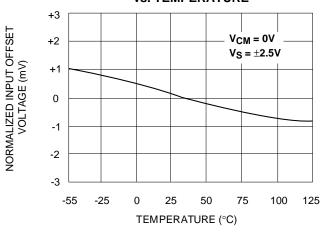
TOTAL SUPPLY CURRENT vs. TOTAL SUPPLY VOLTAGE



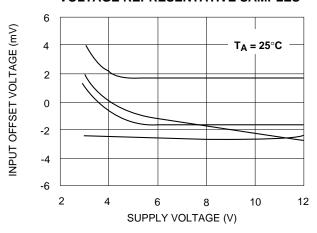
RESPONSE TIME FOR



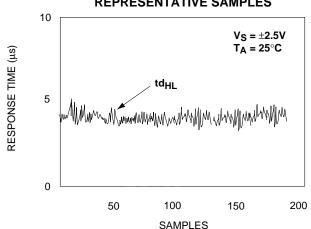
NORMALIZED INPUT OFFSET VOLTAGE vs. TEMPERATURE



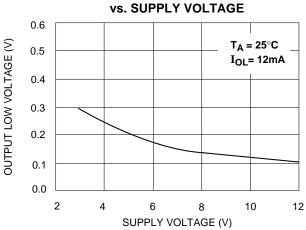
INPUT OFFSET VOLTAGE vs. SUPPLY VOLTAGE REPRESENTATIVE SAMPLES



RESPONSE TIME FOR REPRESENTATIVE SAMPLES

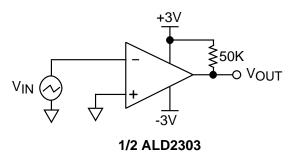


OUTPUT LOW VOLTAGE

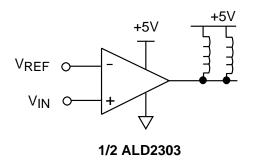


TYPICAL APPLICATIONS

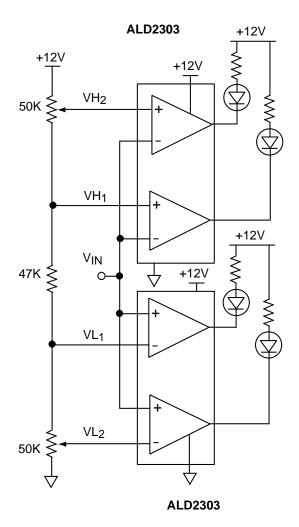
ZERO CROSSING DETECTOR



MULTIPLE RELAY DRIVE

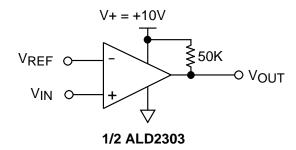


DOUBLE DUAL LIMIT WINDOW COMPARATOR



 VL_1 and VH_1 first limit window send warning VL_2 and VH_2 second limit window execute system cutoff

VOLTAGE LEVEL TRANSLATOR

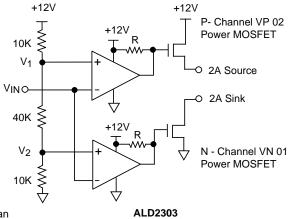


$$V_{REF} = \frac{V^{+}}{2}$$
 for CMOS input

Output V_{OUT} swings from rail-to-rail

TYPICAL APPLICATIONS

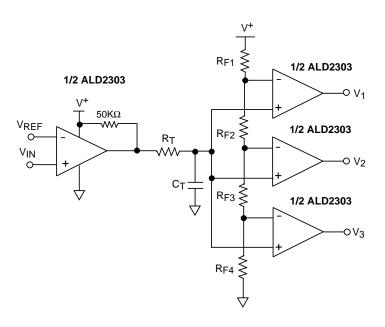
PUSH-PULL COMPLEMENTARY POWER MOSFET DRIVER



$R \ge 50 \text{ K}\Omega$

This circuit eliminates crossover current in the complementary power transistors. The outputs can be used to source and sink different loads or tied together to provide push-pull drive of the same load.

TIME DELAY GENERATOR



Design & Operating Notes:

- 1. In order to minimize stray oscillation, all unused inputs must be tied to ground.
- 2. The input bias and offset currents are essentially input protection diode reverse bias leakage currents, and are typically less than 1 pA at room temperature. These currents are a function of ambient temperature, and would have to be considered in applications where very high source impedance or high accuracy are involved.
- 3. The high output sinking current of 60mA for each output offers flexibility in many applications, as a separate buffer or driver would not be necessary to drive the intended load. However, as the circuit normally operates close to ambient temperature due to its very low power consumption, thermal effects caused by large output current transients must be considered in certain applications.